Electronic Supplementary Information (ESI)

Flexible and highly sensitive pressure sensors based on microcrack arrays inspired by scorpion

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Figure S1 Slit sensillum of scorpion. (a) SEM image shows the silt sensillum positioned in the distal end of the metatarsus. (b) SEM image of the overall slit sensillum.



Figure S2 The crack arrays presented on the top of the petri dish lid. (a), (b) Metallographic microscopic images of the petri dish lid after solvent-induced.



Figure S3 The crack arrays presented on the top of PDMS. (a), (b) Confocal microscopy images show the approximately parallel microcracks in a small visional field.



Figure S4 The reversed pattern of crack arrays presented on the top of PDMS. (a), (b) Confocal microscopy images show the arrangement of the reversed pattern of crack arrays. (c), (d) SEM images showing more details about the reversed pattern of crack arrays.

Microstructure	Sensitivity	Working principle	Response	Ref.
surface	(kPa ⁻¹)a)		time (ms)	
Random	30.1-25.1	piezoresistive	millisecond	1
Distributed			range	
Spinosum				
Hemisphere	5.53-15.14	piezoresistive	40	2
Pyramid 1	0.76	capacitance		3
Pyramid 2	5.53	piezoresistive	0.2	4
Pyramid 3	0.31	piezoelectric	5	5
Cylinder	2.0	piezoresistive	50	6
Pyramid &	0.54-0.58	capacitance	30	7
Cylinder				
Wave	3.8	capacitance	150	8
Pillar	1.8	piezoresistive	100	9
Nanowire 1	5.54	capacitance	unstated	10
Nanowire 2	0.33	piezoresistive	1	11
Pillar & nanowire	6.82	piezoresistive	5	12
Prism	1.8	piezoresistive	10	13
Microgrooves	7.7–41.9	piezoresistive	50	14

Table S1 The comparison of the sensitivities for previous reported pressure sensors.

a) Note that all the sensitivities have defined as an absolute value.

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